



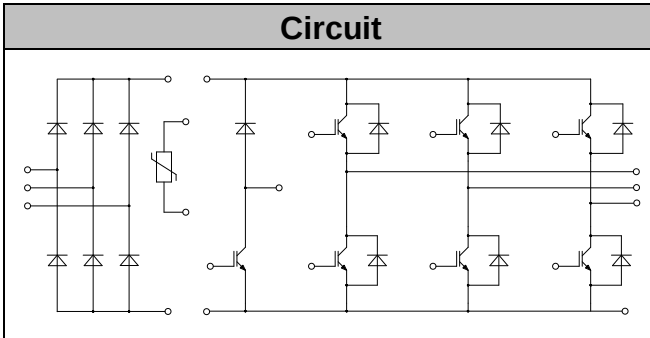
IGBT Modules

V _{CES}	1200V
I _C	40A

Applications

- Motor Drivers
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)

Circuit



Features

- Low switching losses
- Low V_{CE(sat)} with positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- Low inductance case
- High short circuit capability(10us)
- Maximum junction temperature 175°C

● IGBT- inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V _{CES}	V _{GE} =0V, I _C =1mA, T _{vj} =25°C	1200	V
Continuous Collector Current	I _C	T _C =100°C, T _{vjmax} =175°C	40	A
Repetitive Peak Collector Current	I _{CRM}	t _p =1ms	80	A
Gate-Emitter Voltage	V _{GES}	T _{vj} =25°C	± 20	V
Total Power Dissipation	P _{tot}	T _C =25°C T _{vjmax} =175°C	227	W



● IGBT- inverter

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1.2mA, T_{vj}=25^{\circ}C$	5.2	5.9	6.5	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=40A, V_{GE}=15V, T_{vj}=25^{\circ}C$		2.05		V
		$I_C=40A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.20		
		$I_C=40A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.40		
Gate Charge	Q_G			0.35		uC
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=1MHz, T_{vj}=25^{\circ}C$		2.25		nF
Reverse Transfer Capacitance	C_{res}			0.10		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=40A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=27\Omega$ $T_{vj}=25^{\circ}C$		31		ns
Rise Time	t_r			44		ns
Turn-off Delay Time	$t_{d(off)}$			151		ns
Fall Time	t_f			245		ns
Energy Dissipation During Turn-on Time	E_{on}			3.97		mJ
Energy Dissipation During Turn-off Time	E_{off}			2.64		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=40A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=27\Omega$ $T_{vj}=150^{\circ}C$		34		ns
Rise Time	t_r			50		ns
Turn-off Delay Time	$t_{d(off)}$			163		ns
Fall Time	t_f			319		ns
Energy Dissipation During Turn-on Time	E_{on}			5.01		mJ
Energy Dissipation During Turn-off Time	E_{off}			2.95		mJ
SC Data	I_{sc}	$t_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^{\circ}C, V_{CC}=900V, V_{CEM} \leq 1200V$		200		A



● Diode-inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1200	V
Continuous DC Forward Current	I_F		40	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1\text{ms}$	80	A
I^2t -value	I^2t	$V_R=0\text{V}, t_p=10\text{ms}, T_{vj}=125^{\circ}\text{C}$	240	A^2s
		$V_R=0\text{V}, t_p=10\text{ms}, T_{vj}=150^{\circ}\text{C}$	220	

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=40\text{A}, T_{vj}=25^{\circ}\text{C}$		2.00		V
		$I_F=40\text{A}, T_{vj}=125^{\circ}\text{C}$		1.80		
		$I_F=40\text{A}, T_{vj}=150^{\circ}\text{C}$		1.72		
Recovered Charge	Q_{rr}	$I_F=40\text{A}$		2.35		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt = 1000\text{A}/\mu\text{s}$		21		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^{\circ}\text{C}$		0.67		mJ
Recovered Charge	Q_{rr}	$I_F=40\text{A}$		4.26		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt = 1000\text{A}/\mu\text{s}$		23		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=150^{\circ}\text{C}$		1.16		mJ



● IGBT-brake-chopper

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_C	$T_C=100^{\circ}C, T_{vjmax}=175^{\circ}C$	40	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	80	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_C=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	227	W

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1.2mA, T_{vj}=25^{\circ}C$	5.2	5.9	6.5	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=40A, V_{GE}=15V, T_{vj}=25^{\circ}C$		2.05		V
		$I_C=40A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.20		
		$I_C=40A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.40		
Gate Charge	Q_G			0.35		uC
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz, T_{vj}=25^{\circ}C$		2.25		nF
Reverse Transfer Capacitance	C_{res}			0.10		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=40A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=27\Omega$ $T_{vj}=25^{\circ}C$		31		ns
Rise Time	t_r			44		ns
Turn-off Delay Time	$t_{d(off)}$			151		ns
Fall Time	t_f			245		ns
Energy Dissipation During Turn-on Time	E_{on}			3.97		mJ
Energy Dissipation During Turn-off Time	E_{off}			2.64		mJ



Turn-on Delay Time	$t_{d(on)}$	$I_C=40A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=27\Omega$ $T_{vj}=150^\circ C$		34		ns
Rise Time	t_r			50		ns
Turn-off Delay Time	$t_{d(off)}$			163		ns
Fall Time	t_f			319		ns
Energy Dissipation During Turn-on Time	E_{on}			5.01		mJ
Energy Dissipation During Turn-off Time	E_{off}			2.95		mJ
SC Data	I_{sc}	$t_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^\circ C,$ $V_{CC}=900V, V_{CEM} \leq 1200V$		200		A

● Diode-Brake-Chopper

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^\circ C$	1200	V
Continuous DC Forward Current	I_F		15	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1ms$	30	A
I^2t -value	I^2t	$V_R=0V, t_p=10ms, T_{vj}=125^\circ C$	48.0	A ² s
		$V_R=0V, t_p=10ms, T_{vj}=150^\circ C$	42.0	

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=15A, T_{vj}=25^\circ C$		2.00		V
		$I_F=15A, T_{vj}=125^\circ C$		1.80		
		$I_F=15A, T_{vj}=150^\circ C$		1.70		
Recovered Charge	Q_{rr}	$I_F=15A$		1.20		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600V$ $-di_F/dt = 550A/\mu s$		10		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^\circ C$		0.35		mJ
Recovered Charge	Q_{rr}	$I_F=15A$		1.60		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600V$ $-di_F/dt = 550A/\mu s$		15		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=150^\circ C$		1.20		mJ



● Diode-Rectifier

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1600	V
Average output Current 50/60Hz, sine wave	$I_{F(AV)}$	$T_C=100^{\circ}\text{C}$	50	A
Maximum RMS Current at Rectifier Output	I_{RMSM}	$T_C=100^{\circ}\text{C}$	60	A
Surge Forward Current	I_{FSM}	$V_R=0V, t_p=10\text{ms}, T_{vj}=45^{\circ}\text{C}$	320	A
I^2t -value	I^2t	$V_R=0V, t_p=10\text{ms}, T_{vj}=45^{\circ}\text{C}$	510	A^2s

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	V_F	$I_F=40A, T_{vj}=125^{\circ}\text{C}$		1.12		V
Reverse Current	I_R	$T_{vj}=125^{\circ}\text{C}, V_R=1600V$			2.0	mA

● NTC-Thermistor

Characteristic values

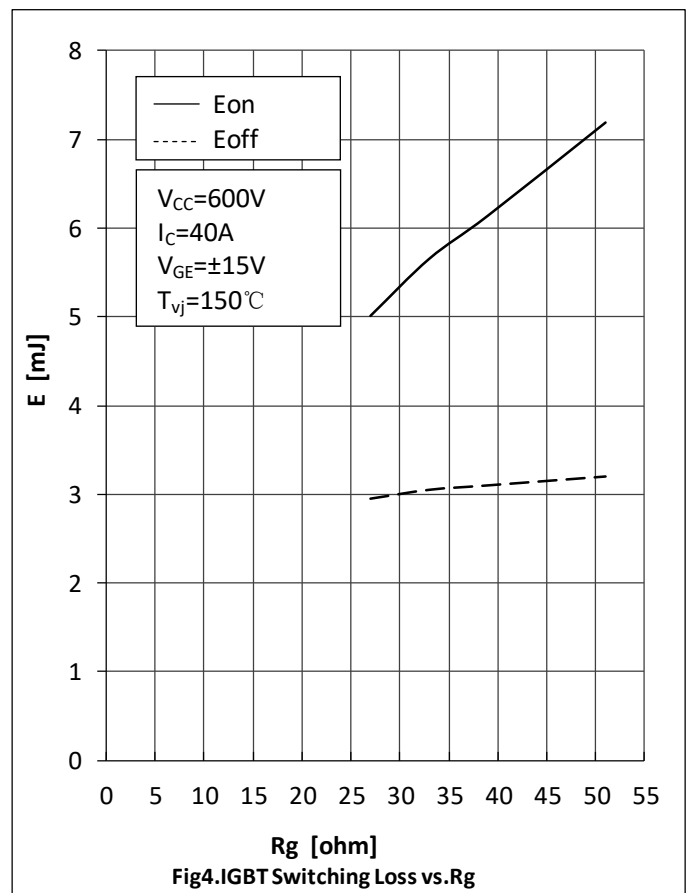
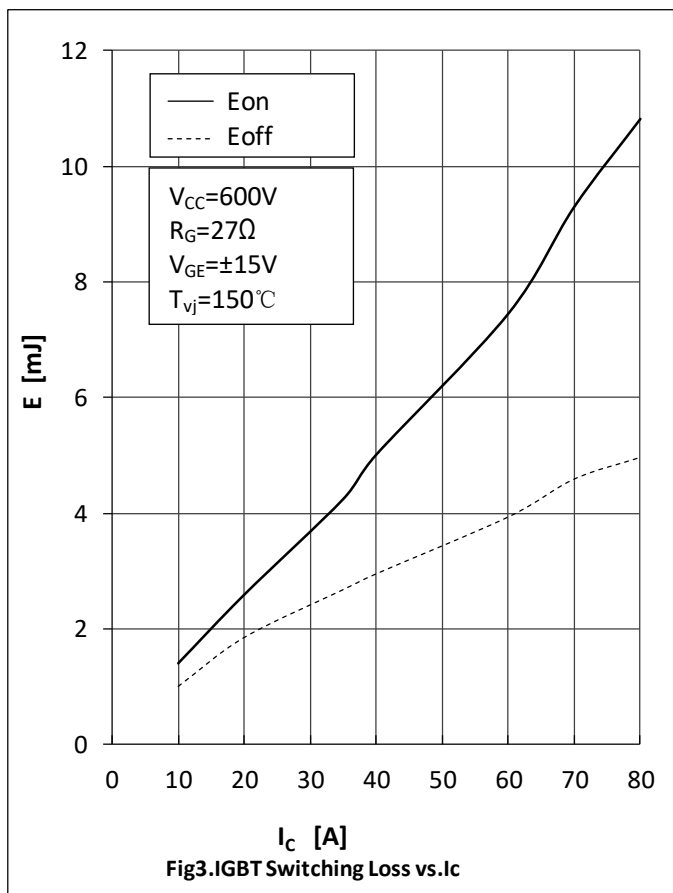
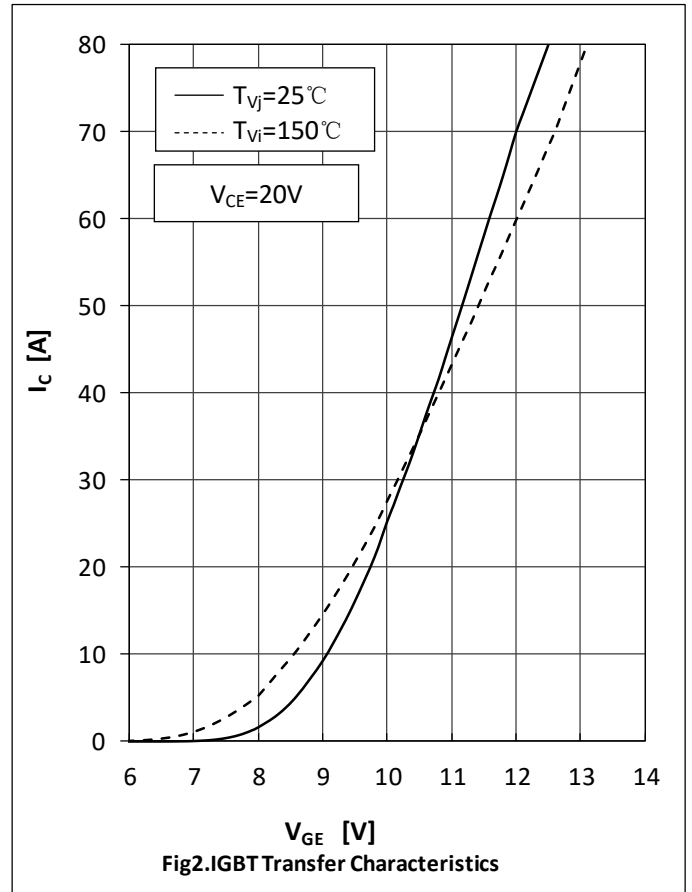
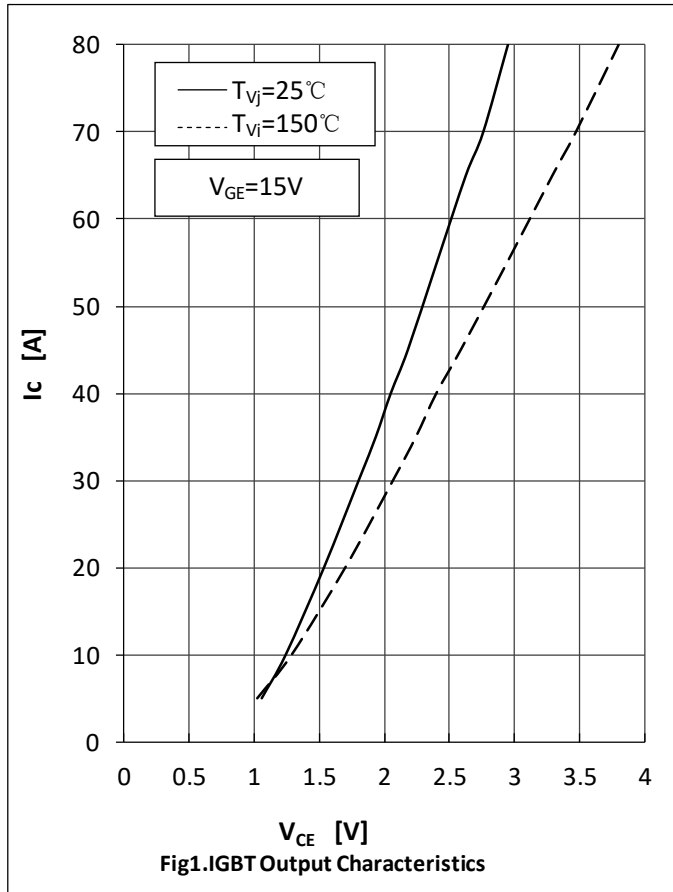
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	R_{25}			5.0		k Ω
Deviation of R100	$\Delta R/R$	$T_C=100, R_{100}=493.3\Omega$	-5		5	%
Power Dissipation	P_{25}				20.0	mW
B-value	$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

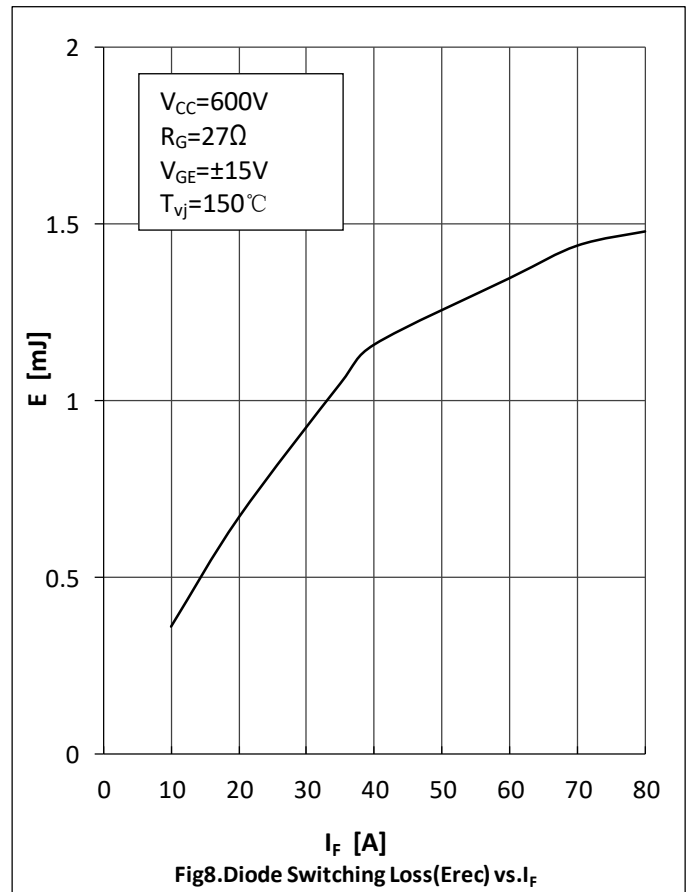
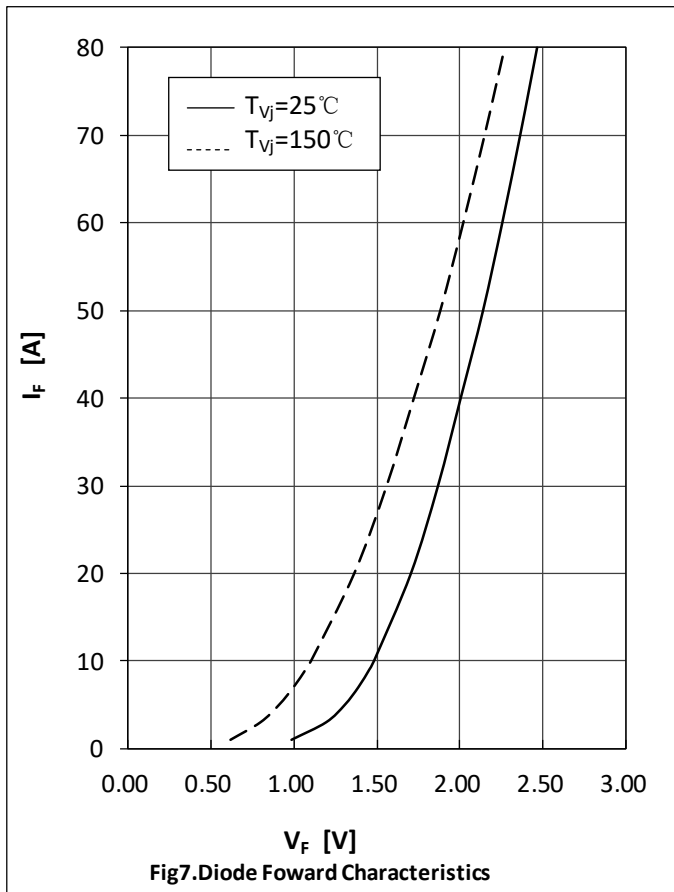
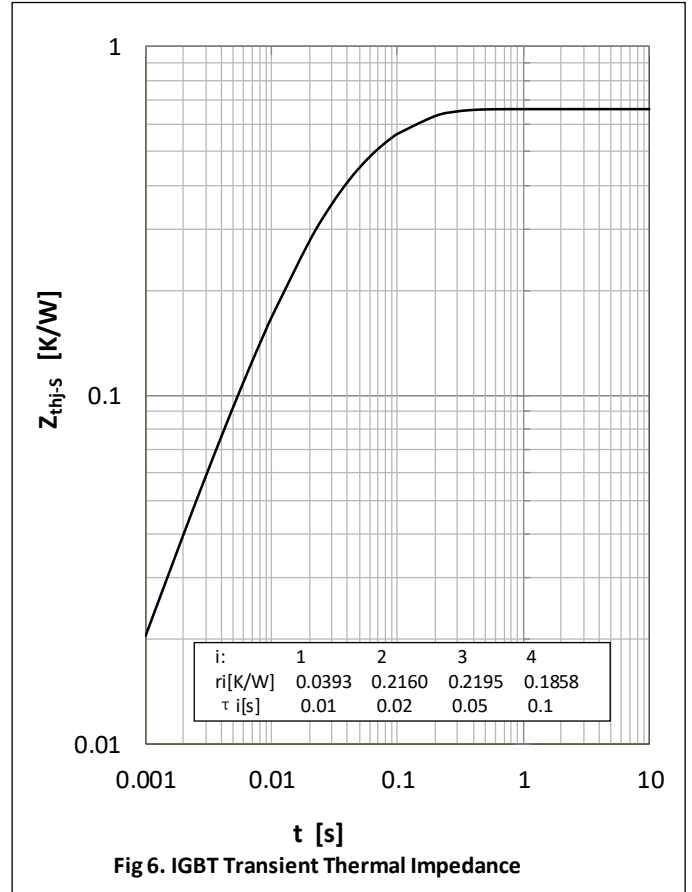
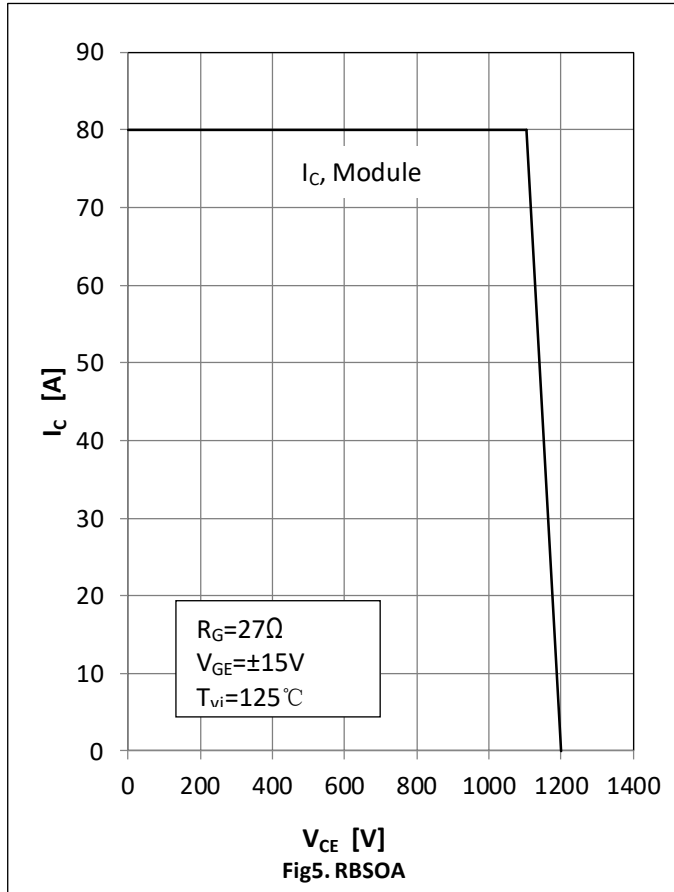


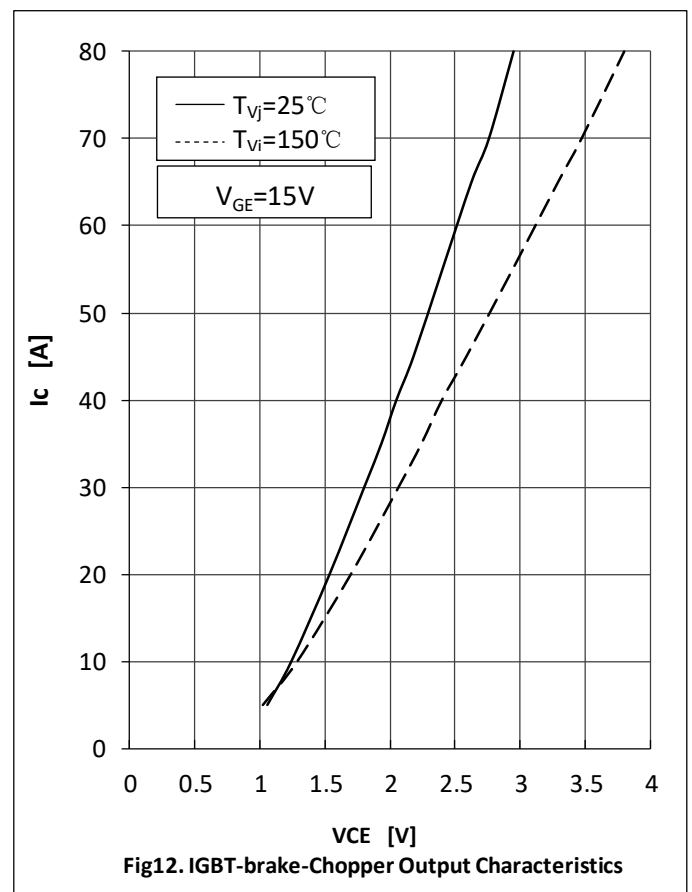
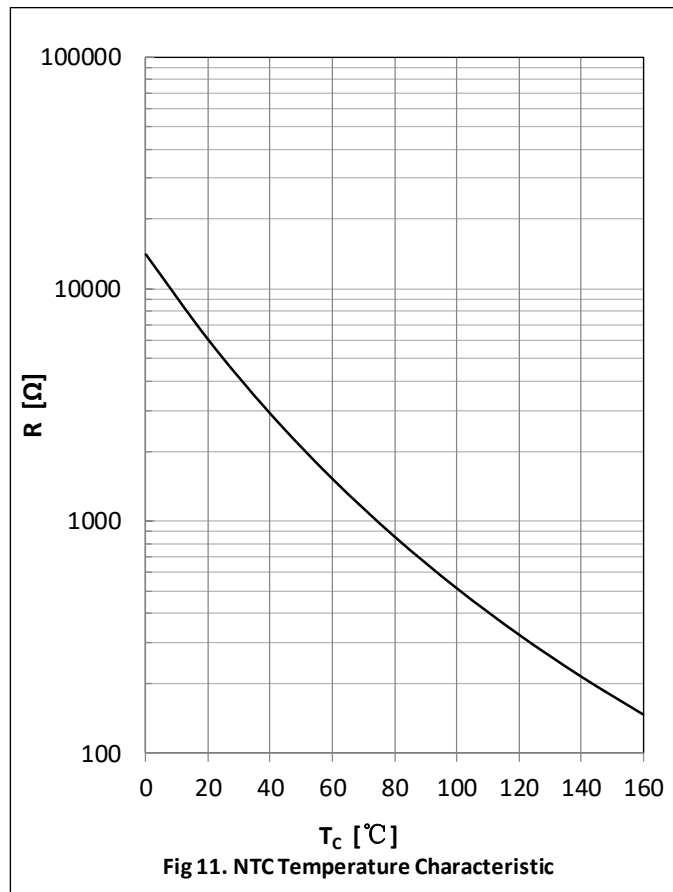
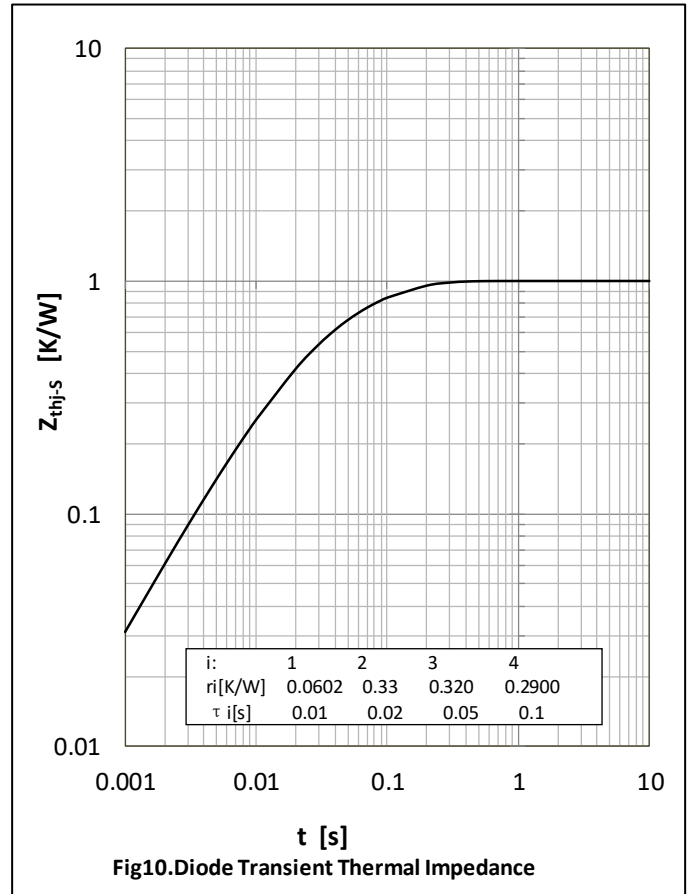
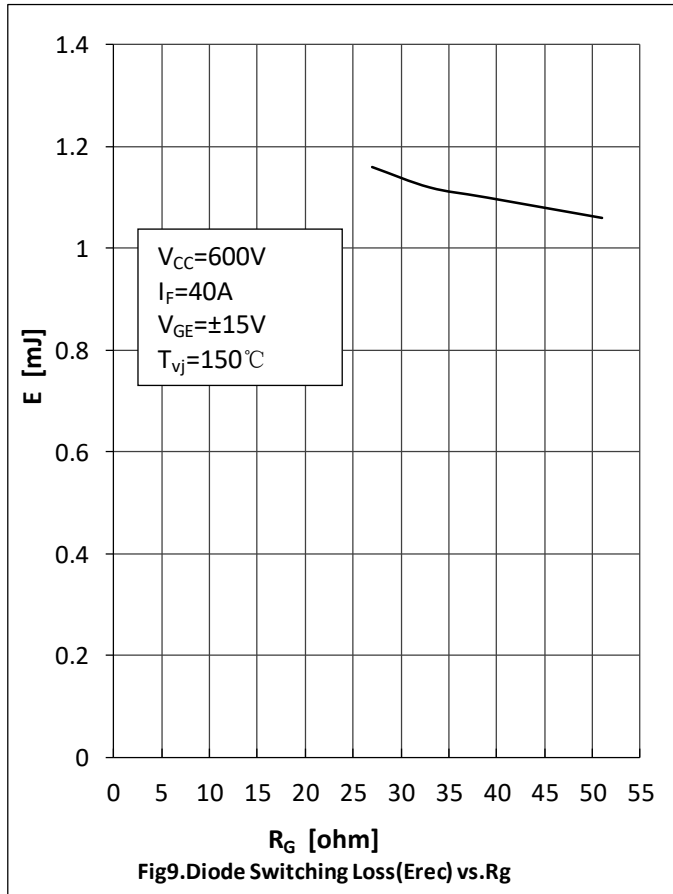
● Module Characteristics

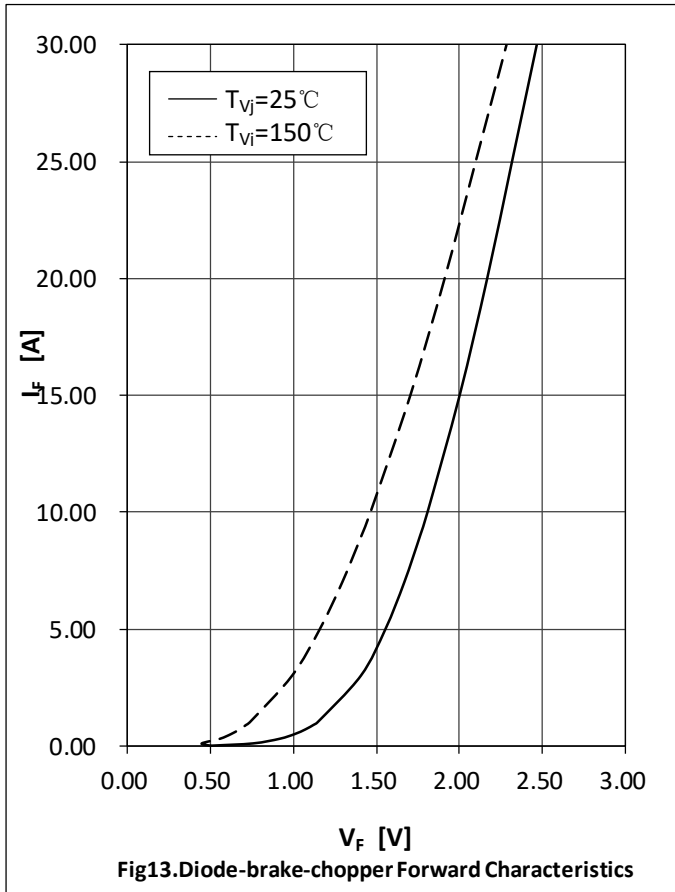
 $T_C=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	V_{isol}	$t=1\text{min}, f=50\text{Hz}$	2500			V
Maximum Junction Temperature	$T_{j\text{max}}$				175	$^{\circ}\text{C}$
Operating Junction Temperature	$T_{j\text{op}}$		-40		150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-40		125	$^{\circ}\text{C}$
Stray-inductance-module	L_{SCE}			60		nH
Module lead resistance, terminals-chip	$R_{\text{CC}'+\text{EE}}$	$T_C=25^{\circ}\text{C}$, per switch		4.0		m Ω
	$R_{\text{AA}'+\text{CC}'}$			3.0		
Thermal Resistance Junction-to Case	$R_{\theta\text{JC}}$	per IGBT-inverter		0.66		K/W
		per Diode-inverter		1.00		
		per IGBT-brake-chopper		0.66		
		per Diode-chopper		1.50		
		per Diode-rectifier		0.75		
Thermal Resistance Case-to Sink	$R_{\theta\text{CS}}$	per IGBT-inverter		0.31		K/W
		per Diode-inverter		0.48		
		per IGBT-brake-chopper		0.31		
		per Diode-chopper		0.70		
		per Diode-rectifier		0.36		
		per Module		0.02		
Module-to-Sink Torque	M_s		3.0		6.0	N·m
Weight of Module	G			180		g



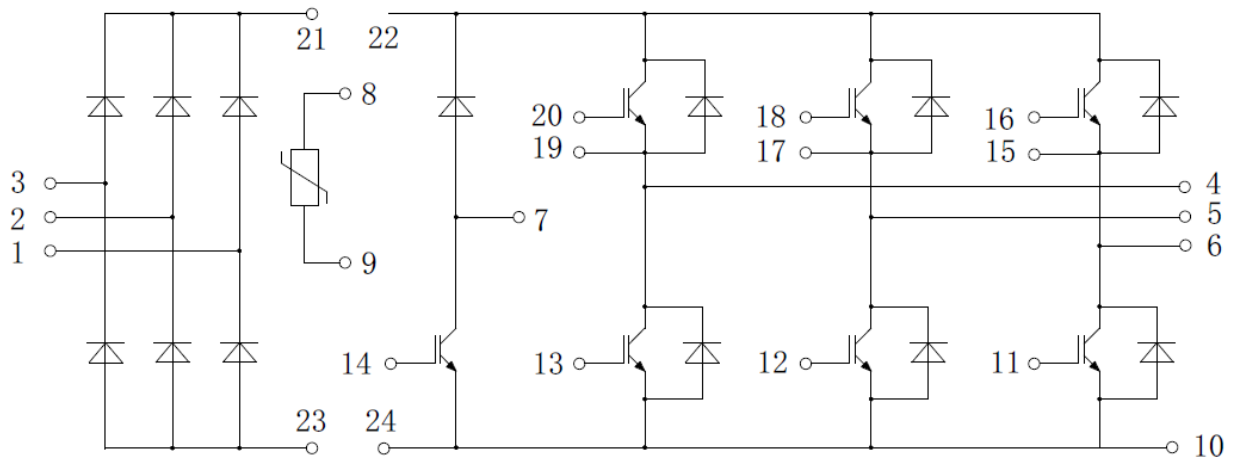




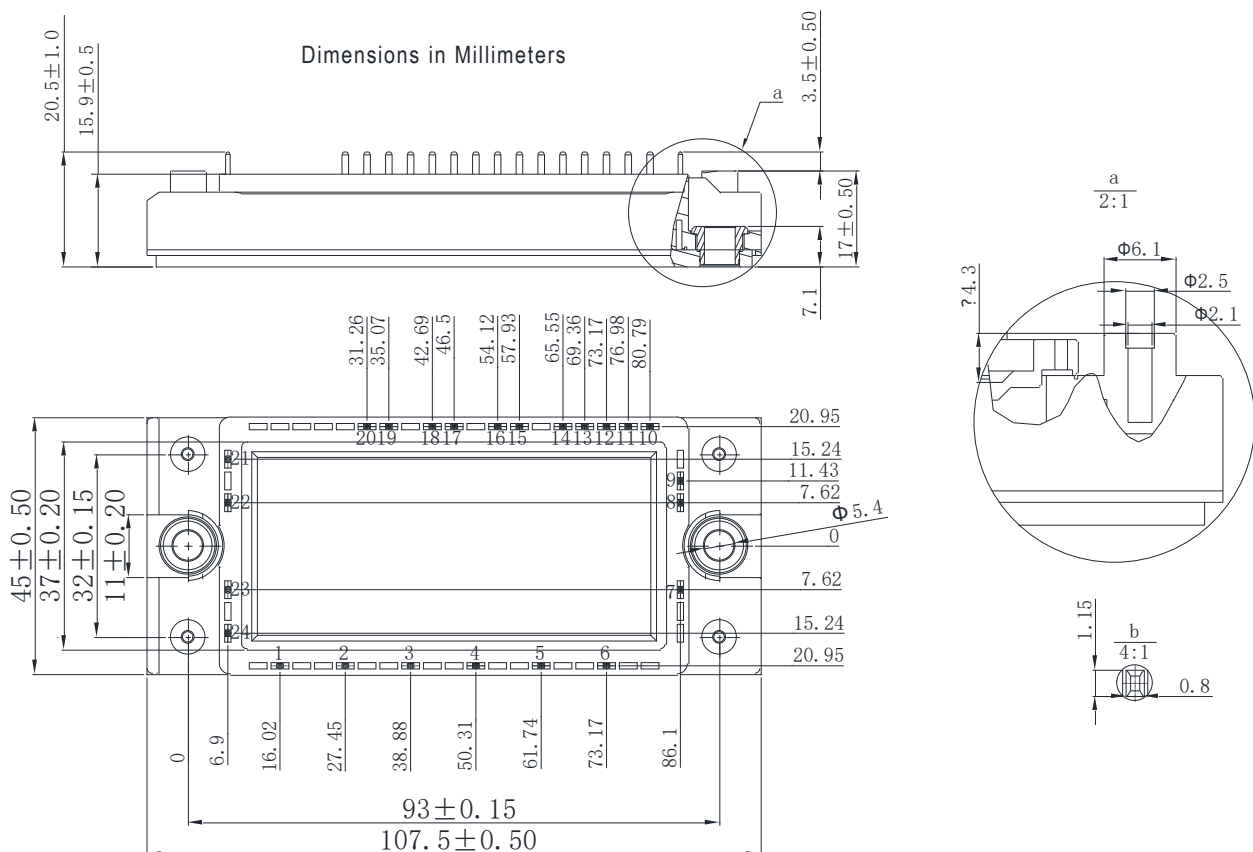




● Circuit Diagram



● Package Outline Information





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